To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HD74HCT563/HD74HCT573

Octal Transparent Latches (with 3-state outputs)

ADE-205-559 (Z)
1st. Edition
Sep. 2000

Description

When the latch enable (LE) input is high, the Q outputs of HD74HCT563 will follow the inversion of the D inputs and the Q outputs of HD74HCT573 will follow the D inputs.

When the latch enable goes low, data at the D inputs will be retained at the outputs until latch enabled returns high again. When a high logic level is applied to the output control input, all outputs go to a high impedance state, regardless of what signals are present at the other inputs and the state of the storage elements.

Features

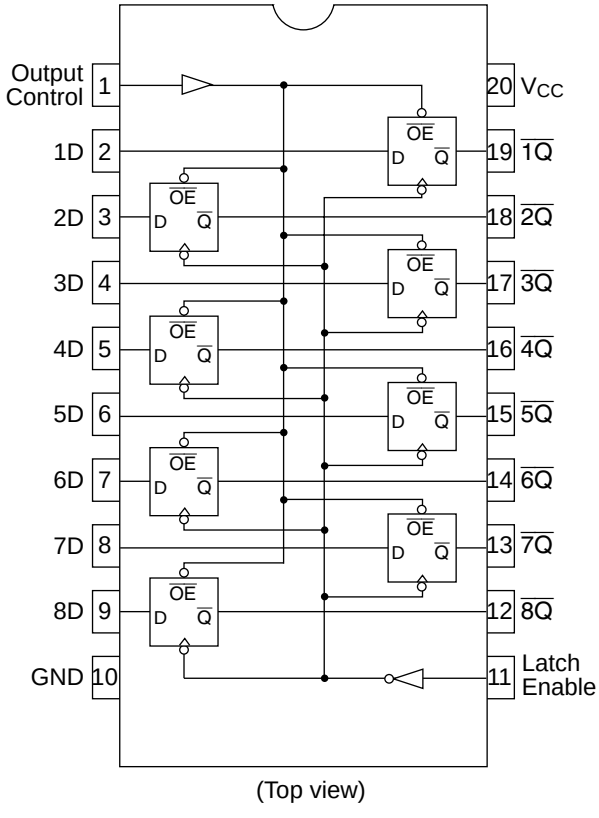
- LSTTL Output Logic Level Compatibility as well as CMOS Output Compatibility
- High Speed Operation: t_{pd} (D to Q, $\overline{Q}$) = 13 ns typ (C_L = 50 pF)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: V_{CC} = 4.5 to 5.5 V
- Low Input Current: 1 μA max
- Low Quiescent Supply Current: I_{CC} (static) = 4 μA max (Ta = 25°C)

Function Table

			Outputs	
Output Control	**Latch Enable**	**Data**	**HD74HCT563**	**HD74HCT573**
L	H	H	L	H
L	H	L	H	L
L	L	X	$\overline{Q}_0$	Q_0
H	X	X	Z	Z

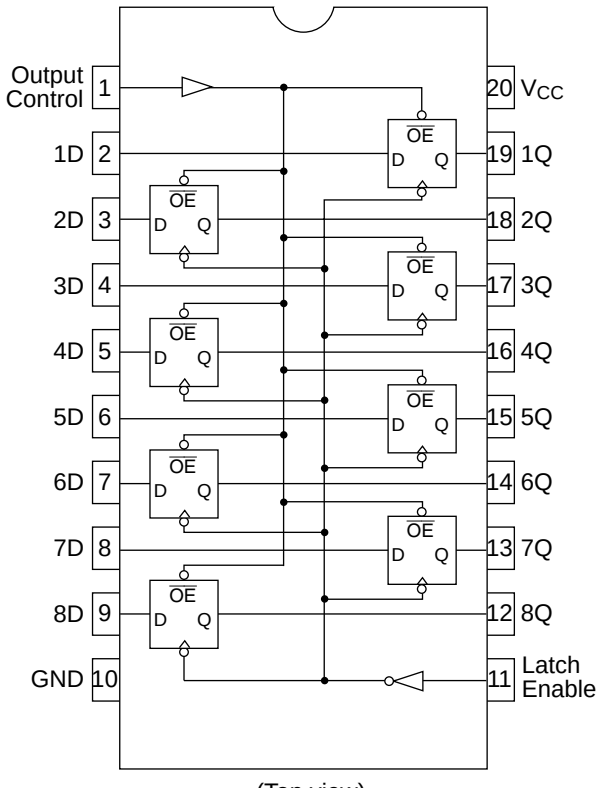
Pin Arrangement

HD74HCT563



(Top view)

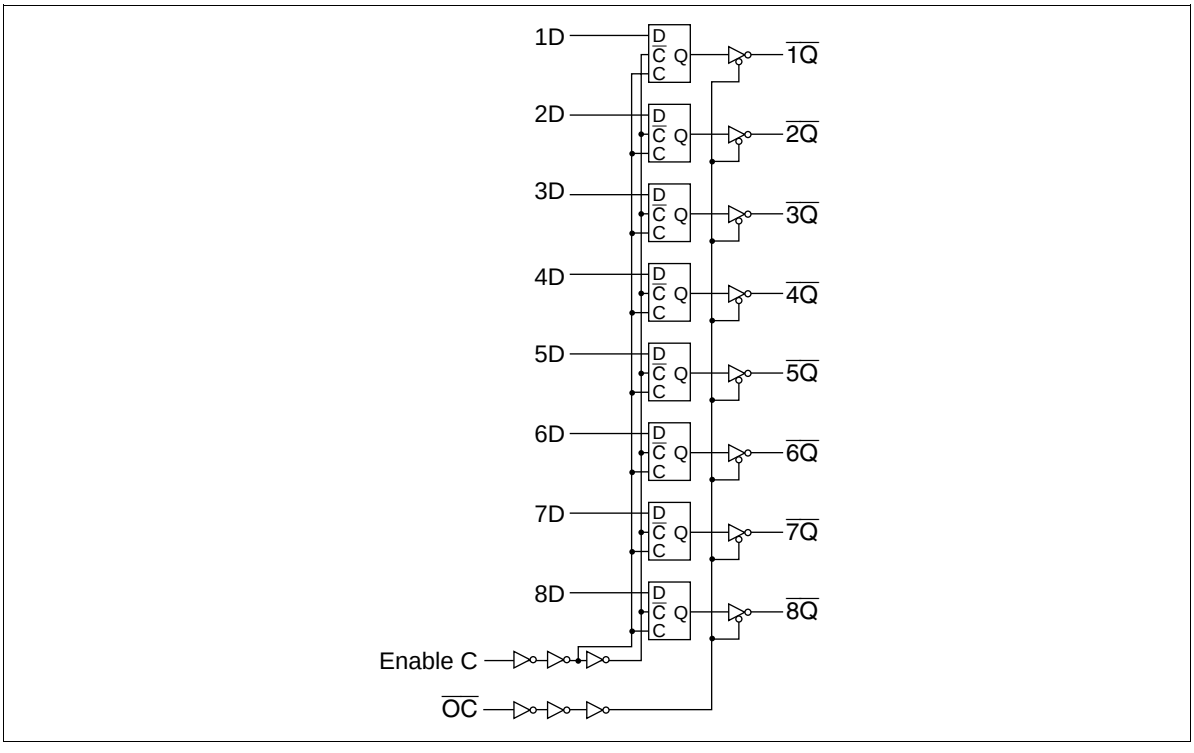
HD74HCT573



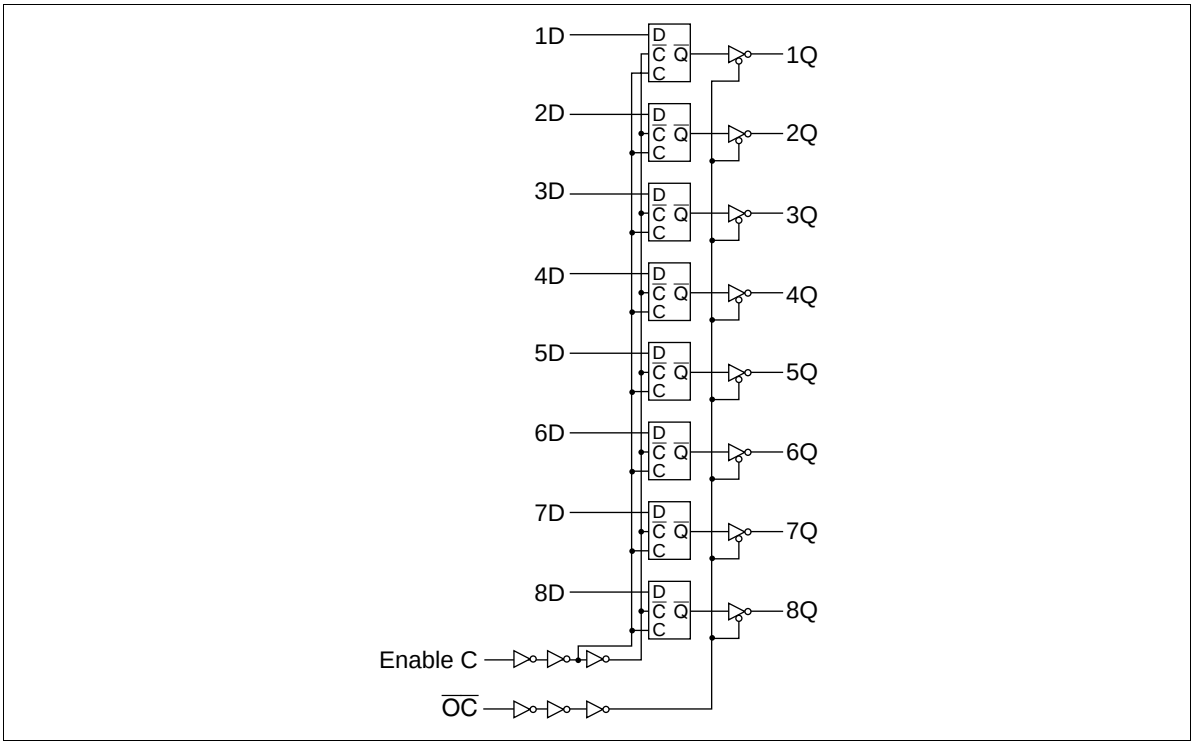
(Top view)

Block Diagram

HD74HCT563



HD74HCT573



Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Supply voltage range	V_{CC}	–0.5 to +7.0	V
Input voltage	V_{IN}	–0.5 to V_{CC} + 0.5	V
Output voltage	V_{OUT}	–0.5 to V_{CC} + 0.5	V
DC current drain per pin	I_{OUT}	±35	mA
DC current drain per V_{CC}, GND	I_{CC}, I_{GND}	±75	mA
DC input diode current	I_{IK}	±20	mA
DC output diode current	I_{OK}	±20	mA
Power dissipation per package	P_T	500	mW
Storage temperature	Tstg	–65 to +150	°C

DC Characteristics

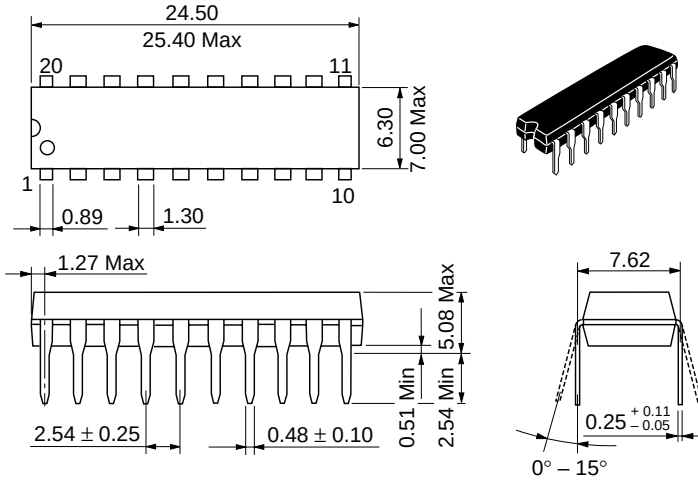
Item	Symbol	Ta = 25°C Min	Typ	Max	Ta = –40 to +85°C Min	Max	Unit	Test Conditions V_{CC} (V)		
Input voltage	V_{IH}	2.0	—	—	2.0	—	V	4.5 to 5.5		
	V_{IL}	—	—	0.8	—	0.8	V	4.5 to 5.5		
Output voltage	V_{OH}	4.4	—	—	4.4	—	V	4.5	Vin = V_{IH} or V_{IL}	I_{OH} = –20 µA
		4.18	—	—	4.13	—		4.5		I_{OH} = –6 mA
	V_{OL}	—	—	0.1	—	0.1	V	4.5	Vin = V_{IH} or V_{IL}	I_{OL} = 20 µA
		—	—	0.26	—	0.33		4.5		I_{OL} = 6 mA
Off-state output current	I_{OZ}	—	—	±0.5	—	±5.0	µA	5.5	Vin = V_{IH} or V_{IL}, Vout = V_{CC} or GND	
Input current	Iin	—	—	±0.1	—	±1.0	µA	5.5	Vin = V_{CC} or GND	
Quiescent current	I_{CC}	—	—	4.0	—	40	µA	5.5	Vin = V_{CC} or GND, Iout = 0 µA	

AC Characteristics (C_L = 50 pF, Input t_r = t_f = 6 ns)

Item	Symbol	Ta = 25°C Min	Typ	Max	Ta = –40 to +85°C Min	Max	Unit	Test Conditions V_{CC} (V)	
Propagation delay	t_{PLH}	—	13	22	—	28	ns	4.5	Data to Q, $\overline{Q}$
time	t_{PHL}	—	13	22	—	28		4.5	
	t_{PLH}	—	14	23	—	29	ns	4.5	Enable G to Q, $\overline{Q}$
	t_{PHL}	—	14	23	—	29		4.5	
Output enable	t_{ZL}	—	14	30	—	38	ns	4.5	
time	t_{ZH}	—	15	30	—	38		4.5	
Output disable	t_{LZ}	—	16	30	—	38	ns	4.5	
time	t_{HZ}	—	17	30	—	38		4.5	
Setup time	t_{su}	15	3	—	19	—	ns	4.5	
Hold time	t_h	5	–1	—	5	—	ns	4.5	
Pulse width	t_w	16	4	—	20	—	ns	4.5	
Output rise/fall	t_{TLH}	—	4	12	—	15	ns	4.5	
time	t_{THL}	—	4	12	—	15		4.5	
Input capacitance	Cin	—	5	10	—	10	pF	—	

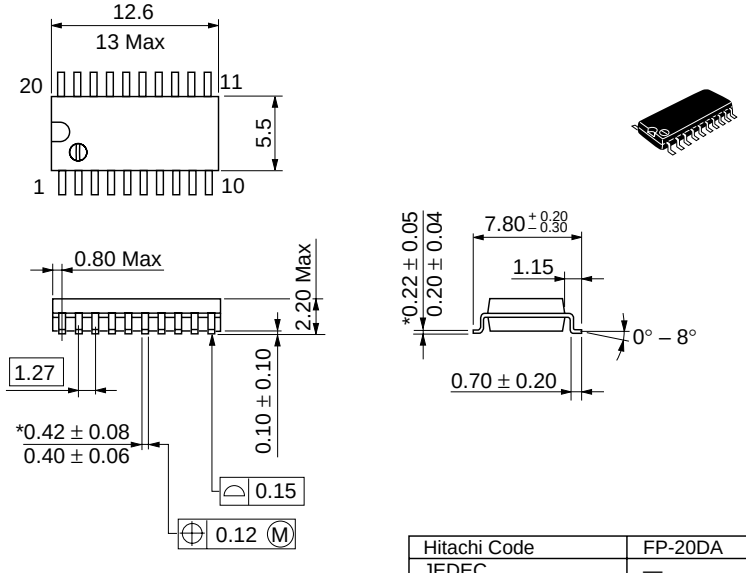
Package Dimensions

Unit: mm



Hitachi Code	DP-20N
JEDEC	—
EIAJ	Conforms
Mass (reference value)	1.26 g

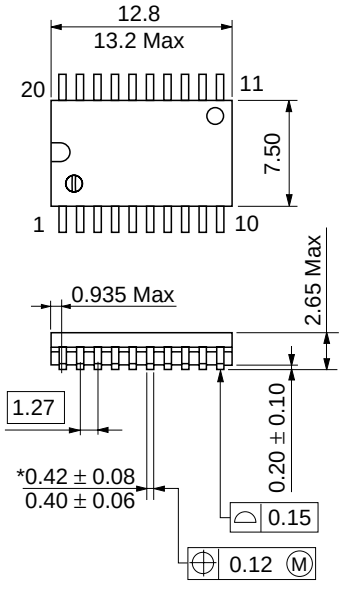
Unit: mm

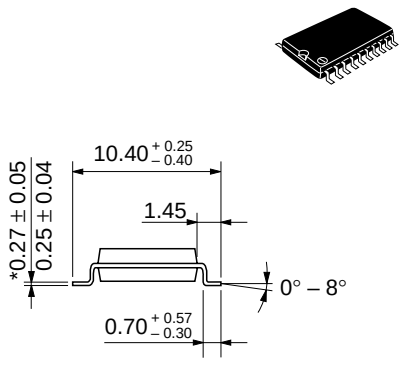


*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DA
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.31 g

Unit: mm

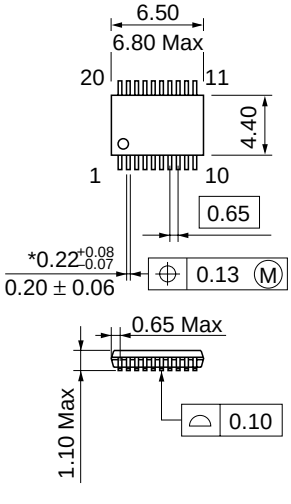


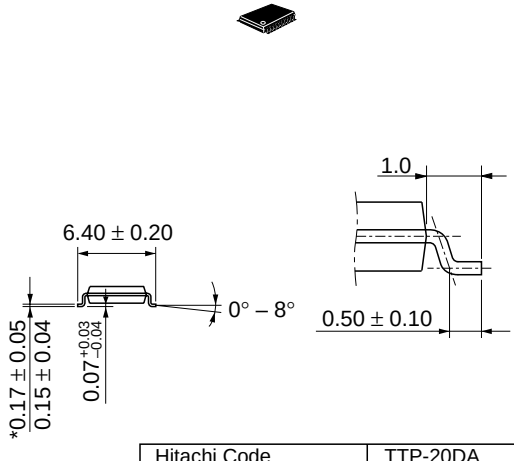


*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DB
JEDEC	Conforms
EIAJ	—
Mass (reference value)	0.52 g

Unit: mm





*Dimension including the plating thickness
Base material dimension

Hitachi Code	TTP-20DA
JEDEC	—
EIAJ	—
Mass (reference value)	0.07 g

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